

Title (en)

METHOD FOR GROWING Si-Ge SEMICONDUCTOR MATERIALS AND DEVICES ON SUBSTRATES

Title (de)

VERFAHREN ZUM ZIEHEN VON SI-GE-HALBLEITERMATERIALIEN UND BAUELEMENTEN AUF SUBSTRATEN

Title (fr)

METHODE DE CROISSANCE PAR EPITAXIE DE MATERIAUX ET DE DISPOSITIFS A SEMI-CONDUCTEURS SI-GE SUR DES SUBSTRATS

Publication

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Application

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Abstract (en)

[origin: WO2006031257A2] A method is provided for growing Si-Ge materials on Si(100) with Ge-rich contents (Ge>50 at.%) and precise stoichiometries SiGe, SiGe<sub

IPC 8 full level

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